

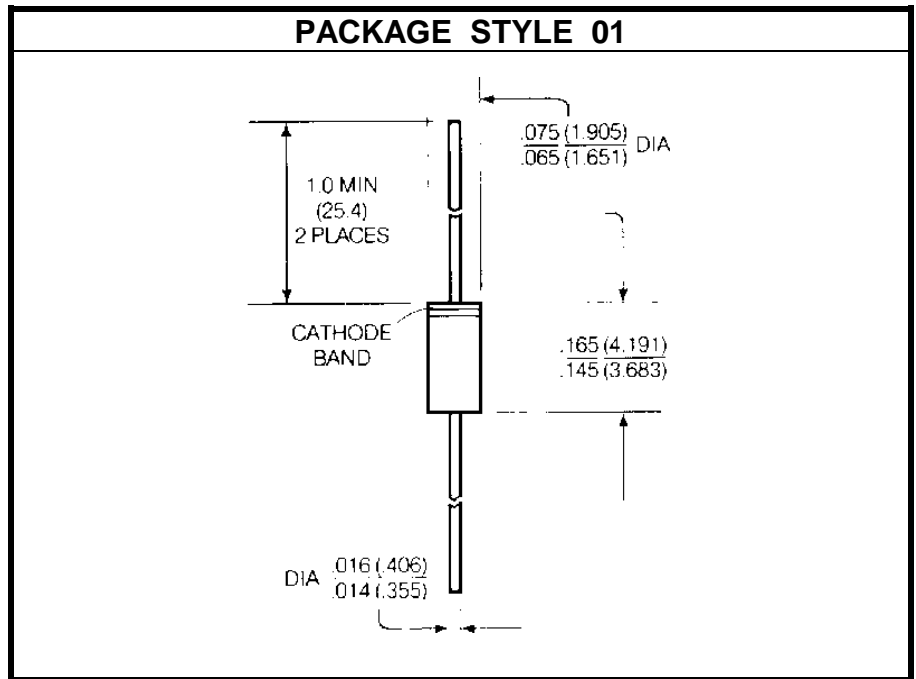
# SILICON PIN DIODE

## DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

## MAXIMUM RATINGS

<b>I<sub>C</sub></b>	100 mA
<b>V<sub>CE</sub></b>	300 V
<b>P<sub>DISS</sub></b>	250 mW @ T <sub>A</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +175 °C
<b>T<sub>STG</sub></b>	-65 °C to +175 °C
<b>θ<sub>JC</sub></b>	20 °C/W



## CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>V<sub>B</sub></b>	I <sub>R</sub> = 10 μA	300			<b>V</b>
<b>C<sub>J</sub></b>	V <sub>R</sub> = 50 V V <sub>R</sub> = 40 V			0.2	<b>pF</b>
<b>C<sub>P</sub></b>			0.10		<b>pF</b>
<b>L<sub>S</sub></b>			1.0		<b>nH</b>
<b>R<sub>S</sub></b>	I <sub>F</sub> = 50 mA			0.6	<b>Ohms</b>
<b>T<sub>L</sub></b>	I <sub>F</sub> = 10 mA    I <sub>R</sub> = 6.0 mA		1000		<b>nS</b>
<b>T<sub>rr</sub></b>	I <sub>F</sub> = 20 mA    I <sub>R</sub> = 100 mA @ 90%		100		<b>nS</b>
<b>I-REGION</b>			30		<b>μM</b>